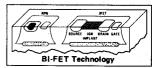


# **Instrumentation Amplifiers**



# LF152/LF252/LF352 FET input instrumentation amplifier

## general description

The LF152 series is the first monolithic JFET input instrumentation amplifier. The well-matched high voltage JFET input devices provide very high input impedance and extremely low bias currents, making the LF152 ideal in applications where high source impedances are encountered.

The LF152 very accurately amplifies a differential input signal and rejects common-mode signal and noise. It is not an op amp, but operates with an internal closed loop gain connection which allows good linearity with no external feedback. The LF152 eliminates the need for extremely precise resistor matching to obtain high common-mode rejection (CMR) and provides high input impedance as compared to the use of conventional op amps connected as a difference amplifier.

The LF152 utilizes internal differential current feedback eliminating the need for precision external feedback components. The amplifier gain can be easily adjusted from 1 to 1000 by changing the value of a single resistor. The transfer function for the LF152 is highly

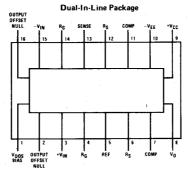
accurate because it has a very low initial gain error and non-linearity. The bandwidth and slew rate are externally controlled and the sense input and device output are pinned out separately for added versatility.

## features

- JFET inputs
- High input impedance
- $2 \times 10^{12} \Omega$ Low bias currents 3 pA
- Low noise currents 0.01 pA rms
- Low gain nonlinearity 0.02%
- High common-mode rejection ratio 110 dB min (G = 100)
- Single resistor gain adjust
- External compensation for extended gain and frequency ranges
- Both input and output offset adjust capability to allow a change of gain without rezeroing
- Low supply current

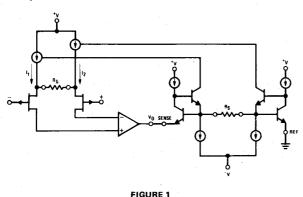
1 mA

# connection diagram

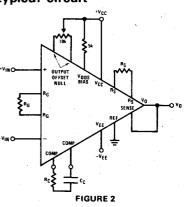


Order Number LF152D, LF252D or LF352D See NS Package D16C

# simplified schematic



## typical circuit



# absolute maximum ratings

Supply Voltage

(Note 1) Cavity DIP (D)

Differential Input Voltage

**Output Short Circuit Duration** 

Maximum Junction Temperature

Lead Temperature (Soldering, 60 seconds)

**Operating Temperature Range** 

Storage Temperature Range

Input Voltage Range

LF152 ±22V ±44V

±22V

Continuous

 $-65^{\circ}$ C  $\leq$  TA  $\leq$  +150 $^{\circ}$ C

300°C

±36V ±18V Continuous

LF252

±18V

 $-65^{\circ}$ C  $\leq$  TA  $\leq$  +150 $^{\circ}$ C

300°C

±36V ±18V Continuous

LF352

±18V

Power Dissipation and Thermal Resistance PD (25°C)

900 mW 100°C/W +150°C  $-55^{\circ}C \le T_{A} \le +125^{\circ}C$ 

 $-25^{\circ}C \le T_{A} \le +85^{\circ}C$ 

900 mW 100°C/W +110°C

900 mW 100°C/W +100°C  $0^{\circ}C \le T_{A} \le +70^{\circ}C$ 

 $-65^{\circ}$ C  $\leq$  TA  $\leq$  +150 $^{\circ}$ C

300°C

dc electrical characteristics (Notes 2 and 3)

PARAMETER		CONDITIONS	
GR	Gain Range	$R_C = 160\Omega$ , $C_C = 0.002\mu$ F	
G	Gain Equation	G = RS/RG	
G₽	Error From Gain Equation	T <sub>Δ</sub> = 25°C, G = 1-100 R <sub>1</sub> =	

TA = 25°C, G = 1-100, RL = 10k ΔG/ΔΤ Gain Temperature Coefficient ٧o Output Voltage Range  $R_L = 2k$ RO Output Resistance VIN Input Voltage Range Input Bias Current TA = 25°C ۱B Input Offset Current 110

Input Resistance

Differential

Input Capacitance

Differential

(RTI) (Note 4)

Common-Mode

Common-Mode

Input Offset Voltage

Supply Sensitivity

Output Offset Voltage

Supply Sensitivity

Reference Input Resistance

Reference Current ·

Supply Current

Temperature Coefficient

Temperature Coefficient

Common-Mode Rejection

Gain Nonlinearity

GNL

RIN

CIN

CMRR

Vios

Voos

IREF

RREF

Is

ΔV<sub>IOS</sub>/ΔT

ΔV<sub>IOS</sub>/ΔV<sub>S</sub>

ΔVOOS/ΔΤ

ΔVOOS/ΔVS

TA = 25°C

TA = 25°C, G = 1 TA = 25°C

TΔ = 25°C

G = 10

G = 100

G = 1000

 $T_A = 25^{\circ}C$ 

TA = 25°C

TA = 25°C

+9 ±10

75

95

110

115

0.02 3 1.2 ±12 3

3

0.5

0.3

2×10<sup>12</sup>

2×10<sup>12</sup>

2.5

5.0

85

105

125

125

8

10

100

600

400

15

500

0.7

LF152

TYP

0.05

MIN

0.1 0.05

20

20

10

2.0

15

200

2.2

MAX

1000

MIN

+9

±10

65

85

100

105

0.05 0.02 3

1.5

±12

3

0.2

0.5

0.05

2x1012

2x1012

2.5

5.0

80

100

120

120

15

10

200

600

800

20

250

1.2

LF252/LF352

TYP

0.2 0.1

40

3

20

0.6

30

400

2.2

MAX

1000

ppm/°C ٧ Ω

UNITS

ν

pΑ nΑ

pΑ nΑ Ω Ω

ρF рF

dB

dΒ

dB

dB

m۷

μV/°C

 $\mu V/V$ 

μV/°C

 $\mu V/V$ 

μA

МΩ

mΑ

m۷

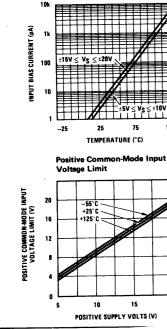
#### ac electrical characteristics (Notes 2 and 3) LF252/LF352 I F152 UNITS CONDITIONS PARAMETER MIN TYP MAX MIN TYP MAX Noise Voltage (RTI) (Note 5) $T_A = 25^{\circ}C$ en 1.3+670/G μVp-p 1.3 f670/G 0.1 Hz - 10 Hz 8+450/G μVrms 81450/G 10 Hz - 10 kHz pArms 0.01 0.01 TA = 25°C, 10 Hz - 10 kHz Noise Current (RTI) (Note 5) in TA = 25°C, ±3 dB GBW Small Signal Bandwidth 140 kHz 140 G = 1 50 kHz 50 G = 10kHz 30 30 G = 1007 kHz G = 1000 $T_A = 25^{\circ}C$ , ±1% Flatness kHz 5 5 G = 1 4 kHz 4 G = 102 kHz 2 G = 100kHz 1.5 G = 1000kHz 25 25 PBW Full-Power Bandwidth V/μs 1 1 SR Slew Rate Settling Time 0.1% TA = 25°C ts 15 us 15 G = 1 15 μs 15 G = 10 40 μs 40 G = 100200 ШS 200 G = 1000Note 1: The maximum power dissipation for these devices must be derated at elevated temperatures and is dictated by T<sub>j</sub> MAX, $\theta_{jA}$ , and the ambient temperature, TA. The maximum available power dissipation at any temperature is PD = (TJ MAX - TA)/6jA or the 25°C PD MAX. Note 2: These specifications apply for $V_S$ = ±15V and over the absolute maximum operating temperature range ( $T_L \le T_A \le T_H$ ) unless otherwise noted. Parameters are specified for $R_C$ = 160 $\Omega$ , $C_C$ = 0.002 $\mu$ F, and a proper layout such as the PC board in Figure 7, which is laid out for Figure 2 and Figure 4.

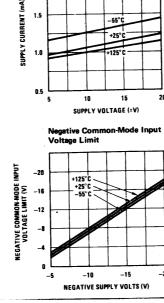
Note 3: If  $V_{OOS}$  adjust is not used, pins 1, 2 and 16 MUST be shorted to  $V_{CC}$ . Note 4: Referred to input (RTI). May be referred to output by subtracting gain in dB. Note 5: Referred to input (RTI). May be referred to output by multiplying by gain G.

125

20

## typical performance characteristics Input Bias Current 2.0

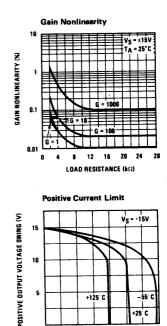




Supply Current

\_65°C

1.5



+125 C

**OUTPUT SOURCE CURRENT (mA)** 

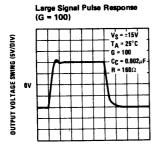
10 15 20 +25 C

25 30

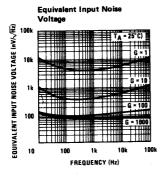
10

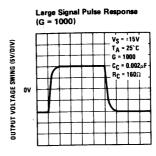
#### typical performance characteristics (con't) Common-Mode Rejection Common-Mode Rejection **Negative Current Limit** Ratio (RTI) Ratio (RTI) NEGATIVE OUTPUT VOLTAGE SWING (V) 160 Vs = ±15V COMMON MODE REJECTION RATIO (4B) 1 kΩ SOURCE UNBALANCE COMMON MODE REJECTION RATIO (48) Vs = ±15V TA = 25°C 120 120 TA = 25°C 100 G = 10 20 60 40 +125°( -55°C 10 15 20 25 30 10 100 14 OUTPUT SINK CURRENT (mA) FREQUENCY (Hz) SOURCE IMPEDANCE UNBALANCE ( $\Omega$ ) Positive Power Supply Rejection Negative Power Supply Rejection Frequency Response Ratio (RTI) Ratio (RTI) 1000 T<sub>A</sub> = 25°C POWER SUPPLY REJECTION RATIO (dB) RATIO (48) Cc = 0.002µF 100 128 G = 1000 120 POWER SUPPLY REJECTION 100 GAIN (V/V) 100 G = 100 G = 100 G = 10 60 40 40 20 0 0 100 101 100k 10 10 FREQUENCY (Hz) FREQUENCY (Hz) FREQUENCY (Hz) Small Signal Pulse Response Small Signal Pulse Response Small Signal Pulse Response (G = 1)(G = 10)(G = 100)OUTPUT VOLTAGE SWING (100 mV/DIV) Vs = ±15V OUTPUT VOLTAGE SWING (180 mV/DIV) VS = ±15V **DUTPUT VOLTAGE SWING (100 mV/DIV)** VS = ±15V TA = 25°C G = 100 TA = 25°C TA = 25°C G = 10 CC = 0.002µF CC = 0.002µF RC = 160Ω Rc = 160Ω TIME (5µs/DIV) TIME (5µs/DIV) TIME (20µs/DIV) Small Signal Pulse Response Large Signal Pulse Response Large Signal Pulse Response (G = 1000)(G = 1)(G = 10)**DUTPUT VOLTAGE SWING (100 mV/DIV)** VS = ±15V VS = 15V V<sub>S</sub> = ±15V **OUTPUT VOLTAGE SWING (5V/D1V)** DUTPUT VOLTAGE SWING (5V/DIV) TA = 25°C TA = 25 C TA = 25°C -G = 1000 G = 10 CC = 0.002µF Cc = 0.002uF Cc = 0.002µF Rc = 160Ω RC = 1600 Rc = 160Ω ٥v 87 TIME (100µs/DIV) TIME (20µs/DIV) TIME (20uS/DIV)

# typical performance characteristics (con't)

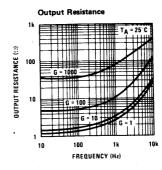


TIME (20µs/DIV)





TIME (100µs/DIV)



## application hints

## **BASIC OPERATION**

The LF152 is a monolithic JFET input differential current feedback instrumentation amplifier. The BIFET process used to fabricate the LF152 makes it possible to take advantage of JFETs throughout the design. In the simplified schematic of Figure 1, the differential input voltage is impressed across resistor RG via the input JFETs, while the difference between the sense and reference voltages is impressed across the resistor RS. The gain of the amplifier is determined by the ratio of resistor RS to resistor RG (G = RS/RG). (For clarity let's follow a signal through the amplifier:)

In Figure 1, let  $R_G=R_S=1~M\Omega$ , the (-) input be grounded, and the (+) input be 1V; the output should be 1V. The 1V signal applied developes  $1\mu A$  through  $R_G$  from right to left and unbalances the current drive to the second stage amplifier. The additional current driven into the (+) input of the second stage amplifier causes the output to increase. As  $V_O$  increases, the sense input voltage increases and the left side of  $R_S$  also increases. When the sense input has risen 1V,  $1\mu A$  will flow through  $R_S$  from left to right and, thus, sub-tract  $1\mu A$  from  $1_T$ . An opposite action simultaneously occurs in 12 which brings the currents into the second stage and thus the system back into balance.

The LF152 series is designed to optimize key parameters in instrumentation amplifiers. The device has very high

common-mode rejection, low gain non-linearity, extremely low bias currents and very high input impedance.

#### **INPUTS**

The P-channel JFET input devices of the LF152 series provide very low bias currents and very high input impedances.

The maximum differential input voltage is independent of the supply voltages, however, neither of the input voltages should be allowed to exceed the negative supply, as this will cause large currents to flow, which can result in a destroyed unit.

Exceeding the negative voltage range on either input will cause a reversal of phase to the output and force the amplifier output to the corresponding high or low state. Exceeding the negative input voltage range on both inputs will force the amplifier output to a high state. Exceeding the positive input voltage range on a single input will not change the phase of the output; however, gain linearity will degrade. If both inputs exceed the positive input voltage range, the output of the amplifier will be forced to a high state.

The common-mode slew rate of the inputs should be limited to  $5V/\mu s$  to insure low input bias currents.

# application hints (con't)

# USING THE SENSE, REFERENCE, AND OUTPUT PINS

The sense input and the output of the device are pinned

out separately to allow increased flexibility in system designs (see applications). The reference input allows biasing of the output voltage, from +10V to -10V. The ac input resistance of both the sense and reference inputs is unusually high because their input currents are forced to be constant with voltage (typically  $20\mu A$ ).

The maximum linear output swing is determined by the magnitude of resistor Rs:

## $|V_{OMAX}| = 10\mu A (R_S)$

If the output of the amplifier is to be abruptly changed more than 6V, a PNP transistor should be connected, as shown in Figure 3, to prevent the slew rate of the output from exceeding the slew rate of the sense stage. If this precaution is not taken, the base-emitter junction of the input transistor in the sense stage will transiently break down and its  $\beta$  will degrade, resulting in a permanent negative shift in output offset voltage.

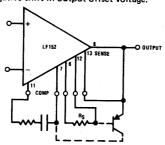


FIGURE 3. Large Signal Transient Suppression

# OFFSET VOLTAGE

Because of the two stage design of the instrumentation amplifier, there are two independent contributors to offset voltage (VOS). The output offset (VOOS) is

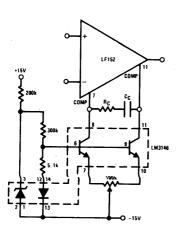


FIGURE 4. Input Offset Adjust

independent of gain while the input offset ( $V_{IOS}$ ) is multiplied by the gain of the amplifier to the output.

## VOS = VIOS (G) + VOOS

The output offset of the LF152 can be adjusted as shown in Figure 2. In addition, the LF152 features input offset adjust which is not common to monolithic instrumentation amplifiers and is normally available only on expensive modules. The simple adjust scheme shown in Figure 5 has only a slight increase in non-linearity compared to that of Figure 4 and is recommended for most applications. Nulling both input and output offset makes the overall offset zero, independent of gain.

The output offset is affected by adjustment of the input offset. For every mV of input offset adjust, the output offset will change by approximately 32 mV. Adjustment of the output offset has no effect on the input offset, so it should always be done last.

Offset adjustment changes the temperature coefficient of the VOS drift. The typical input offset drift of the unadjusted device is  $-10\mu\text{V/}^{\circ}\text{C}$ . If the input offset is adjusted, the VIOS drift increases by approximately

$$V_{IOS}$$
 drift  $\approx -10\mu V/^{\circ}C + 2\mu V/^{\circ}C/(mV)$  of adjustment)

The VOOS drift will be improved by output offset adjust because the magnitudes of the current sources adjusted become less sensitive to VBE variations. If VOOS adjust is not used, pins 1, 2 and 16 must be shorted to the positive supply for circuit operation.

# OFFSET VOLTAGE ADJUSTMENT PROCEDURE

For gains less than 100, only output offset adjustment is needed. For gains greater than 100, input offset adjust is usually necessary since the input offset voltage amplified to the output may be out of the range of the output offset adjust. Input offset adjust is also needed if zero overall offset is desired while varying the amplifier gain.

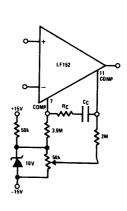


FIGURE 5. Simple Input Offset Adjust

## application hints (con't)

To adjust the input offset, the following procedure should be used:

The effective input offset voltage appears directly across RG when both inputs are connected to ground, and can be measured by a voltmeter referenced to ground. This offset error across RG can be zeroed by the input offset adjustment circuit shown in Figure 4 or 5. The remaining error at the output is strictly due to the output offset voltage which can then be nulled out with the circuit shown in Figure 2. The amplifier is now offset nulled independent of gain.

## COMPENSATION

The variable bandwidth and slew rate of the LF152 are controlled by an RC network between the compensation pins of the amplifier as shown in *Figure 2*. R<sub>C</sub> and C<sub>C</sub> may be varied for optimum operating characteristics in a particular application.

Layout of accompanying circuitry may influence the value of this RC network. The lead lengths to resistors

Rs and R<sub>G</sub> should be minimized and the capacitance from these nodes should also be minimized for optimum frequency response. If R<sub>C</sub> =  $160\Omega$  and C<sub>C</sub> =  $0.002\mu$ F in the printed circuit board of *Figure 7*, the amplifier will be compensated for all gains from 1 to 1000. Gains from 0.1 to 10,000 may be obtained with different compensation.

#### GAIN ERROR AND NONLINEARITY

Gain error of the LF152 is the error between the average slope of the transfer function compared to the slope of R<sub>S</sub>/R<sub>G</sub>. In the LF152, the small gain error is essentially constant with gain and may be nulled out by trimming R<sub>S</sub>.

Of the existing monolithic instrumentation amplifiers, the LF152 is among the lowest in gain nonlinearity error. Gain nonlinearity is the curvature of the transfer function from the theoretically perfect function as shown in *Figure 6*.

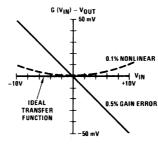


FIGURE 6. Gain Error and Nonlinearity

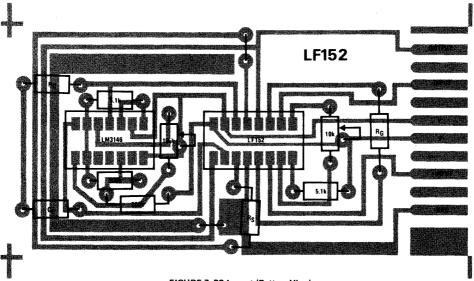
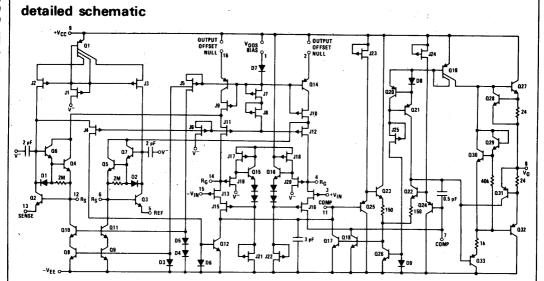
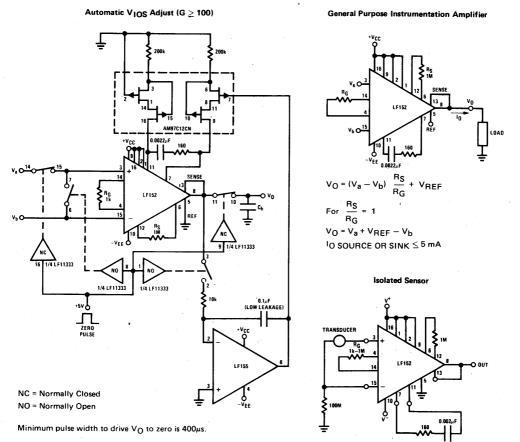


FIGURE 7. PC Layout (Bottom View)



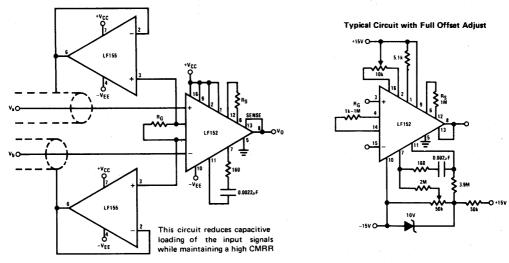
# typical applications



# typical applications (con't) Automatic $V_{OOS}$ Adjust (For $G \le 100$ ) (LOW LEAKAGE CAPACITOR) /4 LF11333

Minimum pulse width to drive  $V_{\mbox{\scriptsize O}}$  to zero is 450 $\mu s$ 

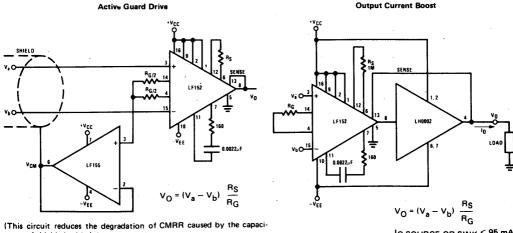
**AC Active Guard Drive** 



NC = Normally Closed

NO = Normally Open

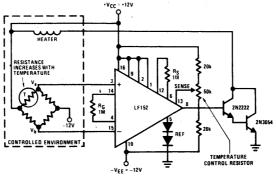
## **Active Guard Drive**



tance of shielded cable.)

O SOURCE OR SINK ≤ 95 mA

## **Temperature Control Circuit**

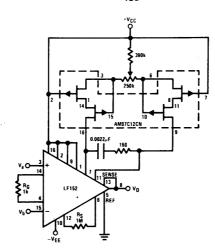


Under balanced conditions, VSENSE - VREF appears across RS, Va - Vb appears across RG and IRG = IRS.

$$\frac{V_a - V_b}{R_G} = \frac{V_{SENSE}}{R_S} \text{ or } V_a - V_b = V_{SENSE} \quad \frac{R_G}{R_S}$$

VSENSE is fixed by the temperature control resistor and  $R_G/R_S$  is constant. The LF152 is used as a comparator with a feedback loop closed through the heater and the temperature dependent resistor. If  $V_a-V_b > VSENSE\ R_G/R_S$ . The output goes high turning "ON" the heater. If  $V_a-V_b < V_{SENSE}\ R_G/R_S$ . The output goes low turning "OFF" the heater.

## Alternate Input Offset (VIOS) Adjust Scheme



## definition of terms

GE

G Closed loop gain.  $G = R_S/R_G$ 

function about the origin.

Gain error. A rotational error of the transfer

GNL Gain nonlinearity. Curvature of the transfer function.

Vos Offset voltage. Voltage offset of the transfer function at the origin Vos = Vios(G) + Voos